

## 20-30GHz Low Noise Amplifier

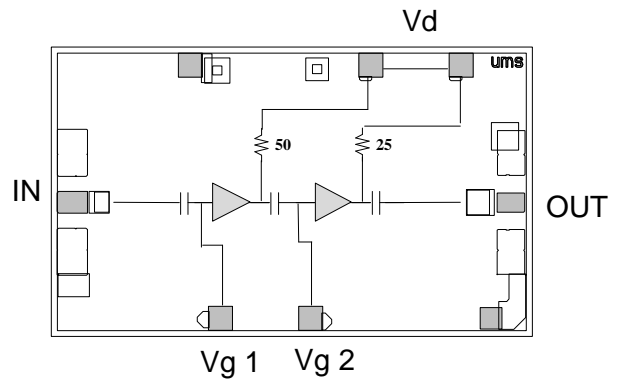
### GaAs Monolithic Microwave IC

#### Description

The CHA2093 is a two-stage wide band monolithic low noise amplifier.

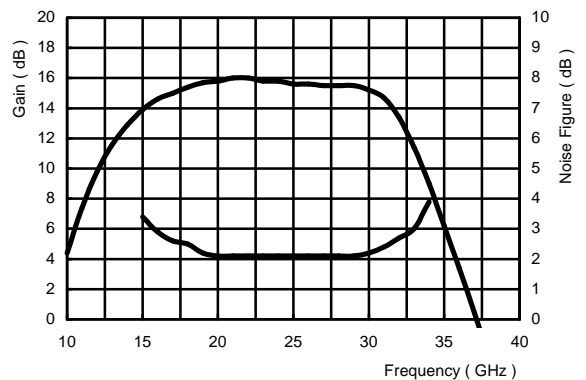
The circuit is manufactured with a standard pHEMT process: 0.25 $\mu$ m gate length, via holes through the substrate, air bridges and electron beam gate lithography.

It is supplied in chip form.



#### Main Features

- Broad band performance 20-30GHz
- 2.2dB noise figure, 20-30GHz
- 15dB gain,  $\pm 0.5$ dB gain flatness
- Low DC power consumption, 50mA
- 20dBm 3rd order intercept point
- Chip size: 1.67 x 1.03 x 0.1mm



*On wafer typical measurements.*

#### Main Characteristics

Tamb = +25°C

Symbol	Parameter	Min	Typ	Max	Unit
NF	Noise figure, 20-30GHz		2.2	3.0	dB
G	Gain	13	15		dB
$\Delta$ G	Gain flatness		$\pm 0.5$	$\pm 1.0$	dB

ESD Protections : Electrostatic discharge sensitive device observe handling precautions !

## Electrical Characteristics

Tamb = +25°C, Vd = +4V Id=45mA

Symbol	Parameter	Min	Typ	Max	Unit
Fop	Operating frequency range	20		30	Ghz
G	Gain (1)	13	15		dB
ΔG	Gain flatness (1)		± 0.5	± 1.0	dB
NF	Noise figure (1)		2.2	3.0	dB
VSWRin	Input VSWR (1)			3.0:1	
VSWRout	Ouput VSWR (1)			3.0:1	
IP3	3rd order intercept point		20		dBm
P1dB	Output power at 1dB gain compression		13		dBm
Id	Drain bias current		50		mA

(1) These values are representative of on-wafer measurements that are made without bonding wires at the RF ports. When the chip is attached with typical 0.15nH input and output bonding wires , the indicated parameter values should be improved.

## Absolute Maximum Ratings (1)

Tamb = +25°C

Symbol	Parameter	Values	Unit
Vd	Drain bias voltage	5.0	V
Pin	Maximum peak input power overdrive (2)	+10	dBm
Top	Operating temperature range	-40 to +85	°C
Tstg	Storage temperature range	-55 to +125	°C

(1) Operation of this device above anyone of these paramaters may cause permanent damage.

(2) Duration < 1s.

## Typical Results

### Chip Typical Response (On wafer Sij)

Tamb = +25°C

Bias Conditions : Vd = +4V Id=45mA

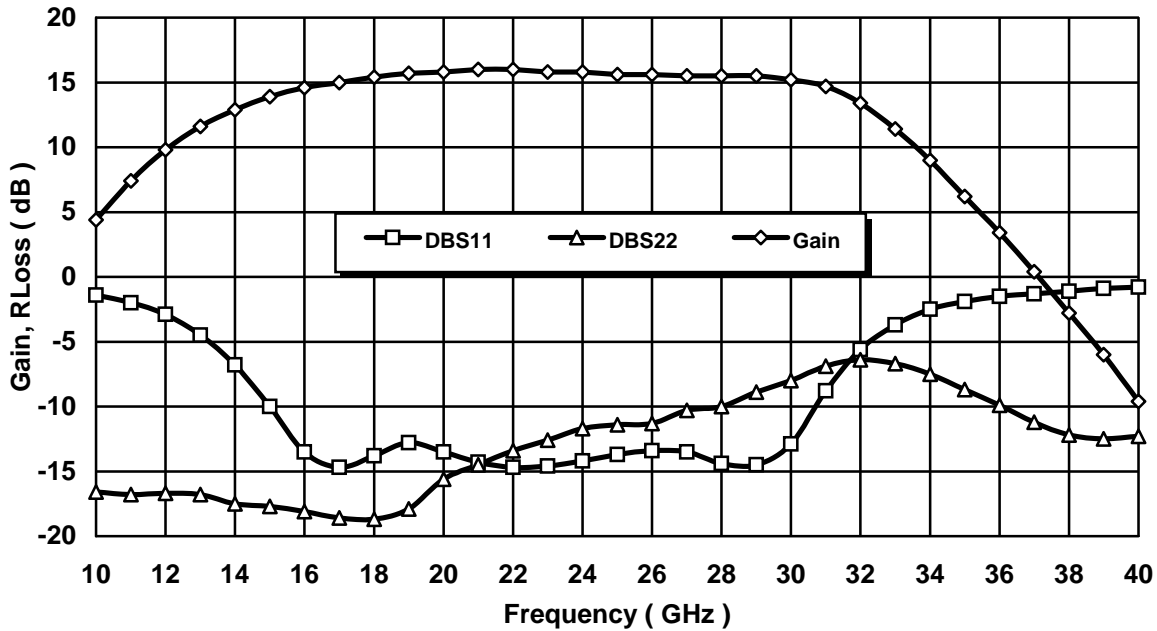
Freq GHz	MS11 dB	PS11 °	MS12 dB	PS12 °	MS21 dB	PS21 °	MS22 dB	PS22 °
10	-1.36	140	-62.29	-138.5	4.35	51.6	-16.6	151.6
11	-1.98	121.9	-58.39	-130.1	7.36	27.2	-16.75	145.1
12	-2.93	101.1	-53.05	-130.3	9.77	0.8	-16.67	137.9
13	-4.5	77.7	-49.08	-146.8	11.61	-26.2	-16.77	129.8
14	-6.8	50.1	-46.97	-163.9	12.9	-53.2	-17.47	122.7
15	-10.02	16.4	-44.52	173.2	13.86	-78.7	-17.67	122.2
16	-13.47	-30	-42.23	160.2	14.55	-103.5	-18.06	118.4
17	-14.68	-86	-40.43	138.2	15	-127	-18.55	118.4
18	-13.76	-131	-39.41	126.2	15.36	-149.8	-18.7	125.4
19	-12.83	-159.2	-38	104.7	15.69	-171.8	-17.9	131.3
20	-13.51	177.8	-36.01	92.4	15.79	165.6	-15.62	131.1
21	-14.3	170.9	-34.99	63.7	15.96	144.3	-14.48	127
22	-14.74	167.2	-34.53	46.8	15.98	122.3	-13.4	120.5
23	-14.63	168	-34.46	24.6	15.84	102.1	-12.6	116.3
24	-14.15	163.4	-33.67	6.3	15.75	80.9	-11.67	107.1
25	-13.71	155.8	-33.27	-7.6	15.6	60.2	-11.4	100.6
26	-13.42	145.5	-32.65	-29.3	15.55	40.3	-11.3	96.1
27	-13.54	124.4	-32.6	-51.5	15.46	18.6	-10.33	91.6
28	-14.43	100.2	-32.49	-68.3	15.48	-2.8	-9.98	85.7
29	-14.48	56.9	-31.69	-88.8	15.48	-27.3	-8.88	80.2
30	-12.87	5.6	-31.87	-115.7	15.24	-53	-7.99	70.5
31	-8.84	-37.4	-31.22	-140.4	14.69	-82.2	-6.86	58.1
32	-5.55	-73.3	-31.23	-171	13.43	-112.8	-6.35	40.1
33	-3.72	-101.3	-32.96	159.7	11.43	-141.9	-6.69	20.4
34	-2.5	-123.2	-34.73	134.8	9.01	-168.7	-7.51	1.5
35	-1.88	-141.2	-35.69	121.6	6.2	167.5	-8.65	-17
36	-1.52	-155.7	-35.69	98	3.35	145.9	-9.92	-36.6
37	-1.32	-167.5	-37.95	72.2	0.36	125.7	-11.17	-56.5
38	-1.07	-177.6	-38.15	56.8	-2.78	107.4	-12.15	-78.9
39	-0.93	172.6	-43.41	86.9	-6.02	89	-12.5	-103.1
40	-0.82	164.7	-43.1	76.9	-9.59	71.9	-12.27	-127.3
41	-0.68	157.2	-43.1	44.4	-13.6	55.3	-11.82	-148.5
42	-0.52	149.5	-43.23	39.6	-18.24	40.2	-10.89	-166.3
43	-0.5	142	-44.08	24	-24.6	27.2	-9.87	-179.6
44	-0.41	135.3	-45.8	21	-35.19	30.1	-8.91	167.4
45	-0.37	128.4	-45.05	18.1	-37.14	126.8	-8.04	156.2

Typical Results

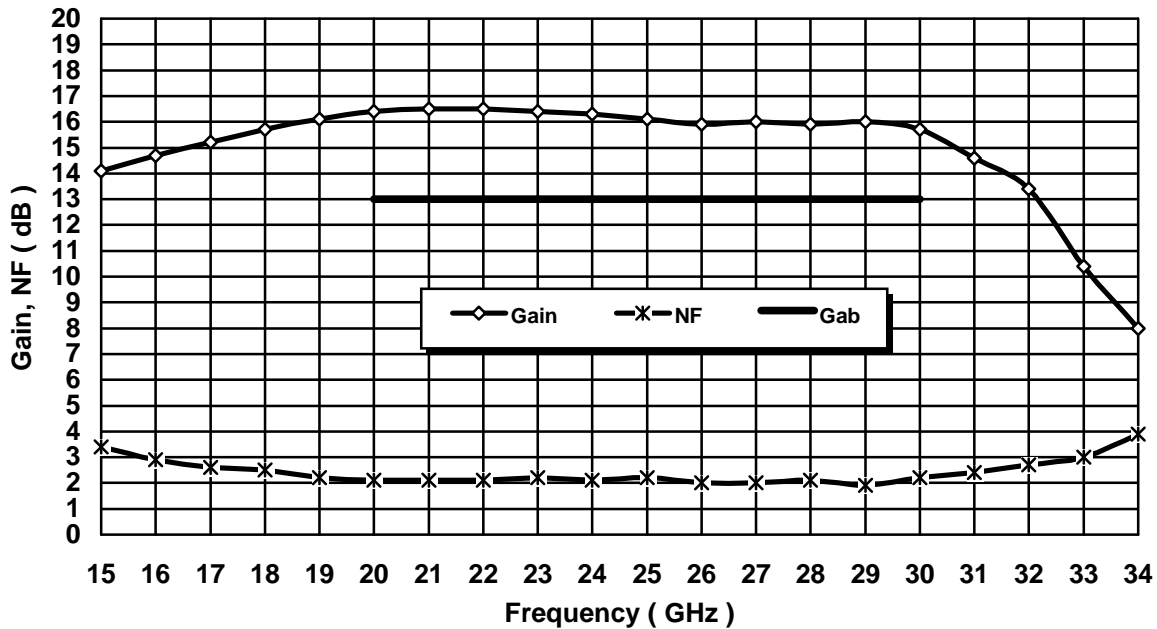
Chip Typical Response ( On wafer Si ) :

Tamb = +25°C

Vd = 4V ; Id = 45mA



Typical Gain and Matching measurements on wafer.

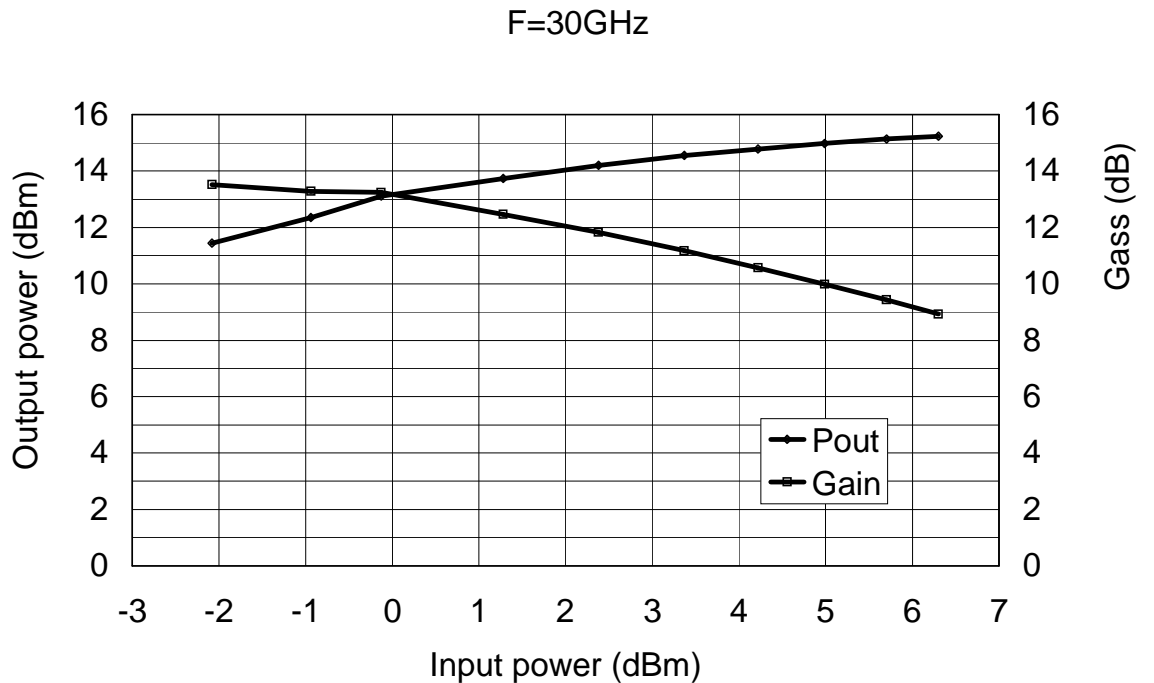
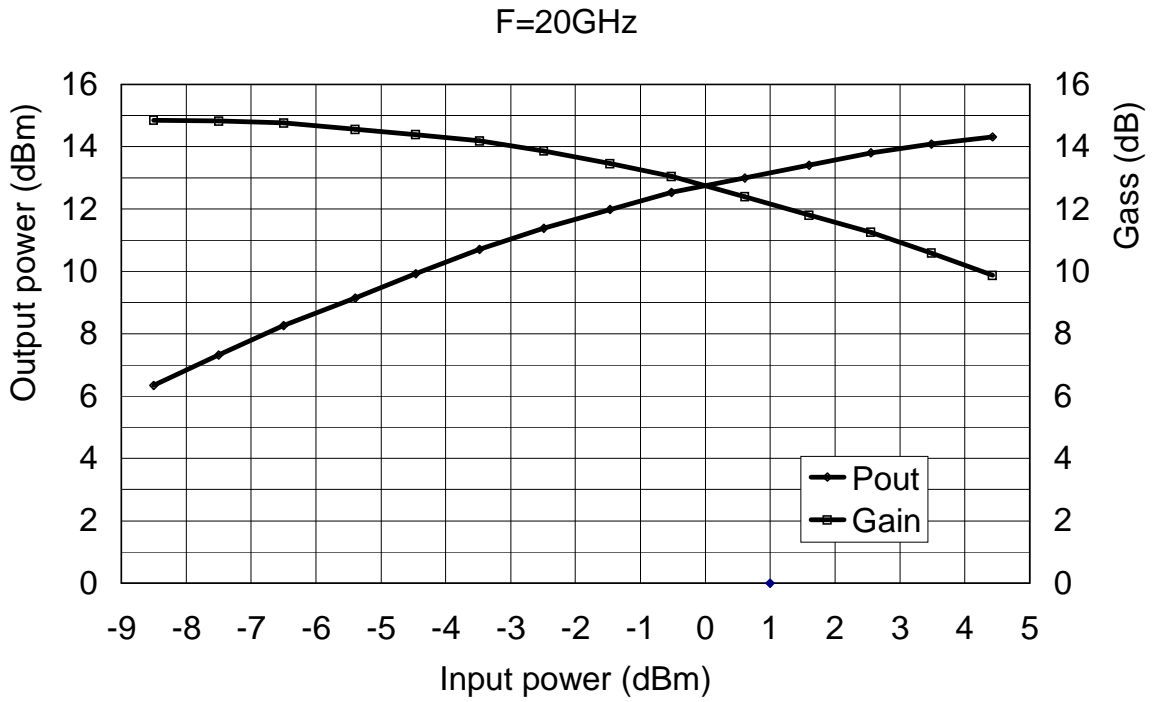


Typical Gain and Noise Figure measurements on wafer

**Typical Results**

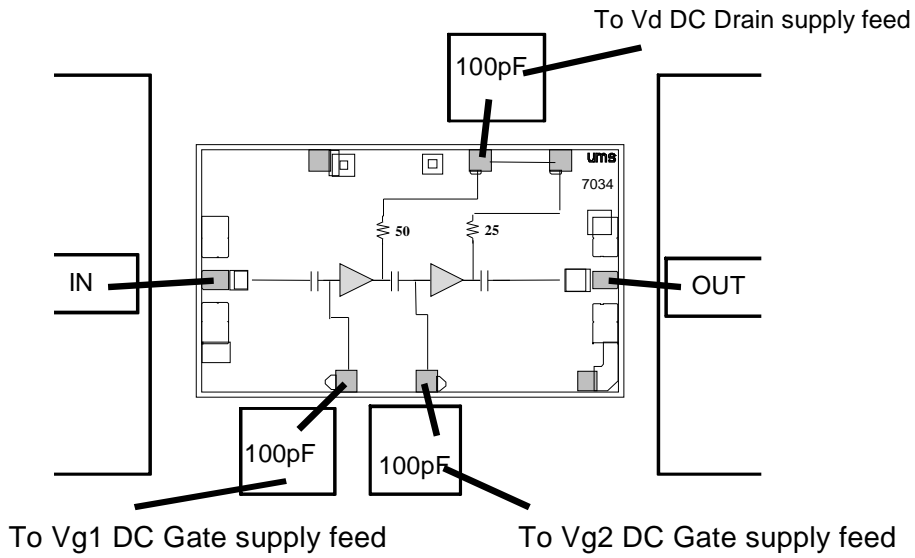
Tamb = +25°C

Vd = 4V ; Id = 45mA

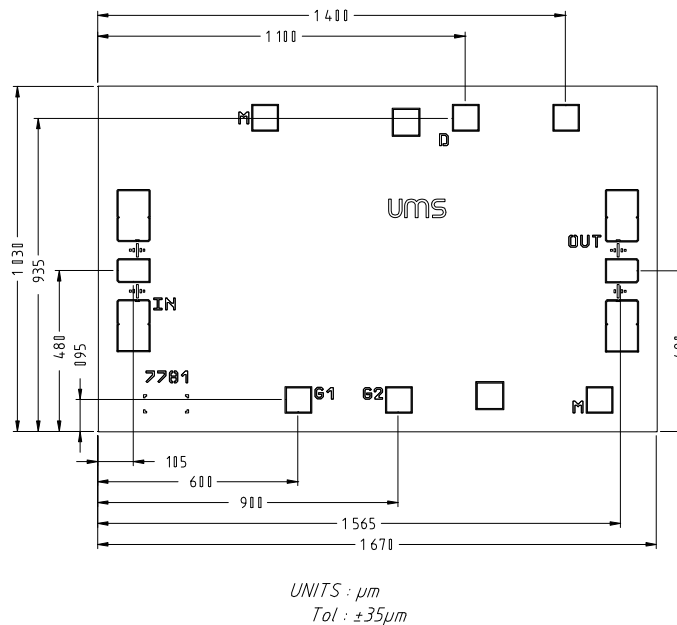


**Typical Output Power and Gain measurements in test jig  
(included losses of the jig)**

## Typical Chip Assembly

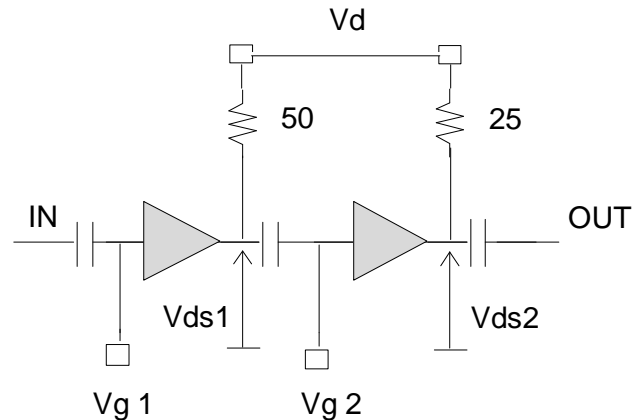


## Mechanical data



## Chip Biasing

This chip is a two stage amplifier, and flexibility is provided by the access to number of pads. The internal DC electrical schematic is given in order to use these pads in a safe way.



The two requirements are:

- N°1: Not exceed  $V_{ds} = 3.5V$  (internal Drain to Source voltage)
- N°2: Not biased in such a way that  $V_{gs}$  becomes positive. (internal Gate to Source voltage)

We propose two standard biasing:

Low Noise and low consumption:  $V_d = 3.5V$  and  $I_d = 30mA$  ( $V_{g1}=V_{g2}$ )

Low Noise and high output power:  $V_d = 4.0V$  and  $I_d = 45mA$ . A separate access to the gate voltages of the first and the output stage is provided. Nominal bias is obtained for a typical current of 30mA for the output stage and 15 mA for the first stage. The first step to bias the amplifier is to tune the  $V_{g1} = -1V$  and  $V_{g2}$  to drive 30mA for the full amplifier. Then  $V_{g1}$  is reduced to obtain 45 mA of current through the amplifier.

## Ordering Information

Chip form : CHA2093-99F/00

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